



Features

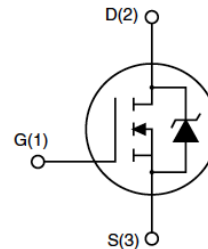
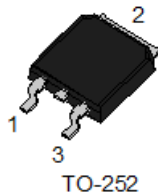
- 100V,15A
- $R_{DS(ON)} = 95m\Omega$ (Typ.) @ $V_{GS} = 10V$
- $R_{DS(ON)} = 100m\Omega$ (Typ.) @ $V_{GS} = 4.5V$
- Low Total Gate Charge
- Low Reverse Transfer Capacitance
- Improved dv/dt Capability
- Fast Switching Speed

Product Summary

V_{DS}	100	V
$R_{DS(on),TYP} @ V_{GS}=10 V$	95	m Ω
I_D	15	A

Application

- Uninterruptible Power Supply(UPS)
- Inverter System



Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	15
		$T_C = 100^\circ C$	10
I_{DM}	Pulsed Drain Current ^{note1}	60	A
P_D	Power Dissipation	$T_C = 25^\circ C$	55
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.72	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	3.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=10V, I_D=10A$	-	95	110	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	100	130	m Ω
g_{FS}	Forward Transconductance	$V_{GS}=5V, I_D=4A$	2	-	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, f=1.0\text{MHz}$	-	932	-	pF
C_{oss}	Output Capacitance		-	37	-	pF
C_{rss}	Reverse Transfer Capacitance		-	21	-	pF
Q_g	Total Gate Charge	$V_{DS}=80V, I_D=10A$	-	19.2	-	nC
Q_{gs}	Gate-Source Charge		-	3.4	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	6.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=10V, V_{DD}=50V, R_L=2.8\Omega, R_{REN}=6\Omega, I_D=10A$	-	12.6	-	ns
t_r	Turn-on Rise Time		-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	32.5	-	ns
t_f	Turn-off Fall Time		-	4.3	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	15	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	60	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=10A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

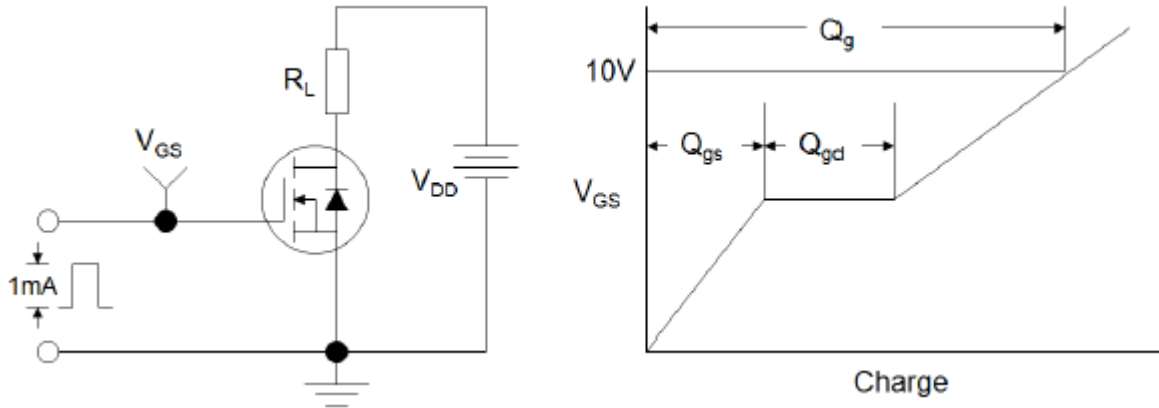


Figure 1: Gate Charge Test Circuit & Waveform

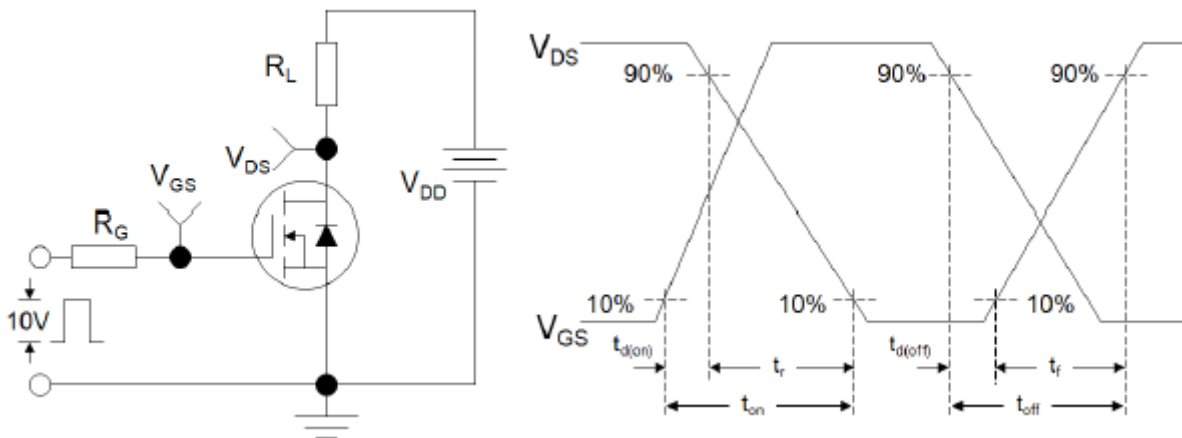


Figure 2: Resistive Switching Test Circuit & Waveforms

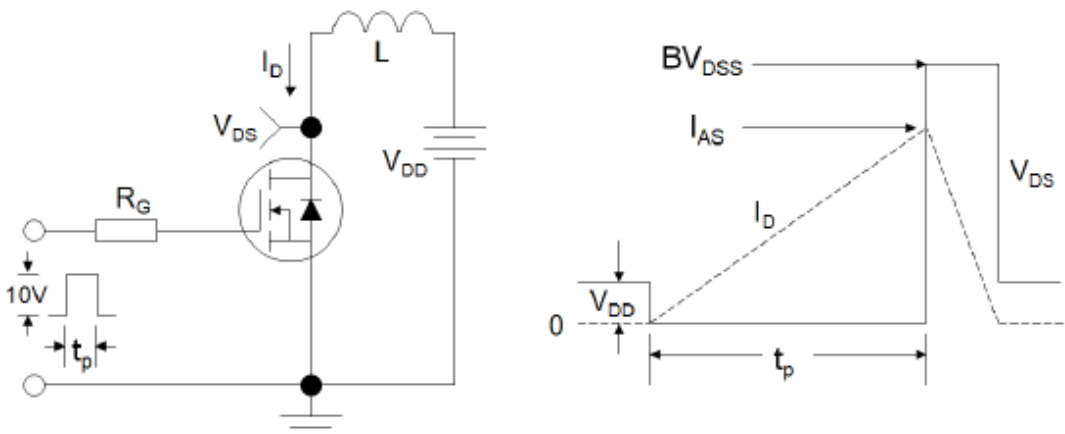


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

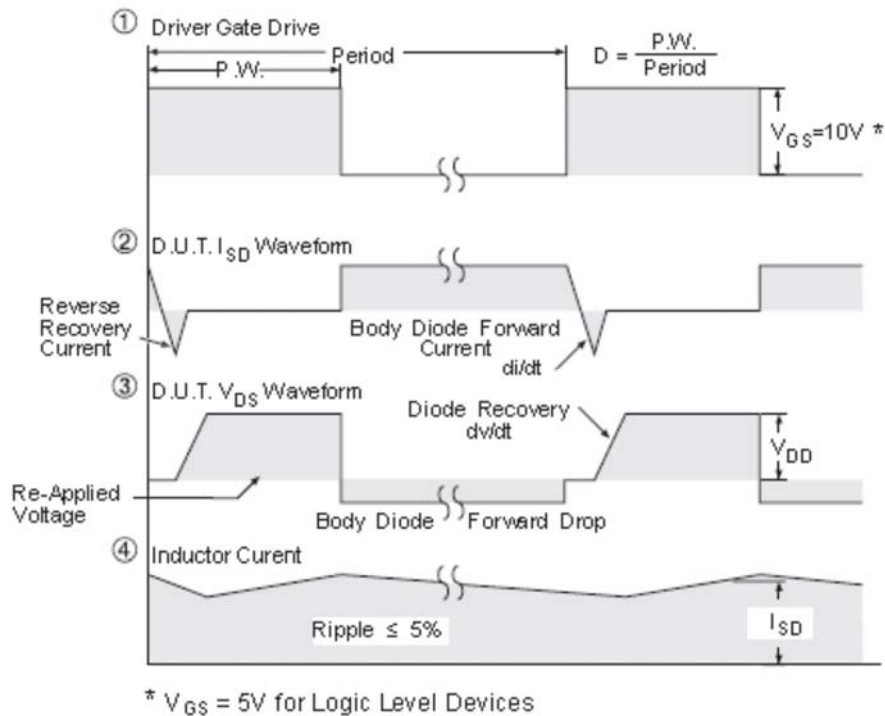
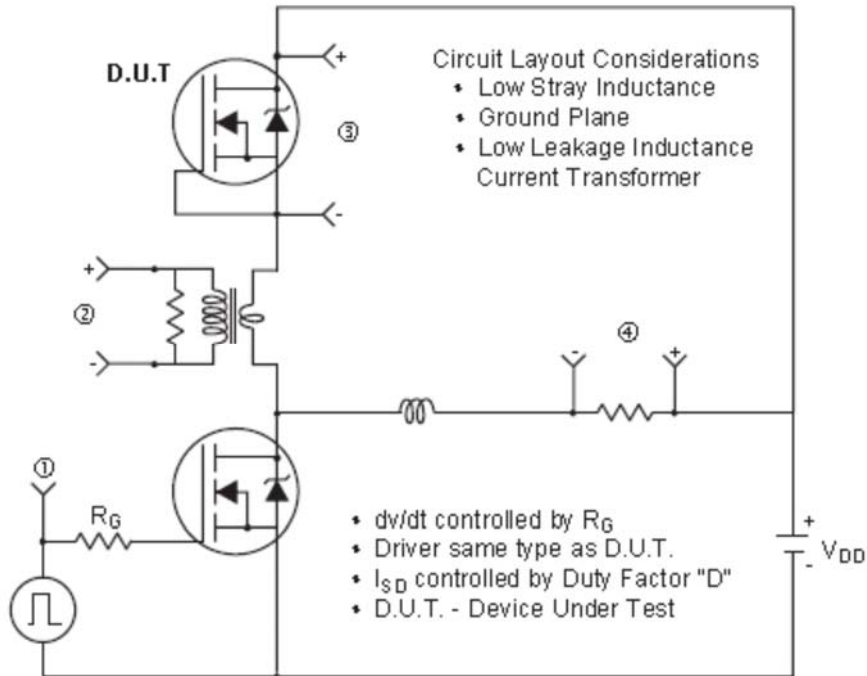
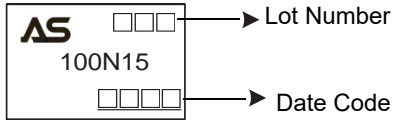


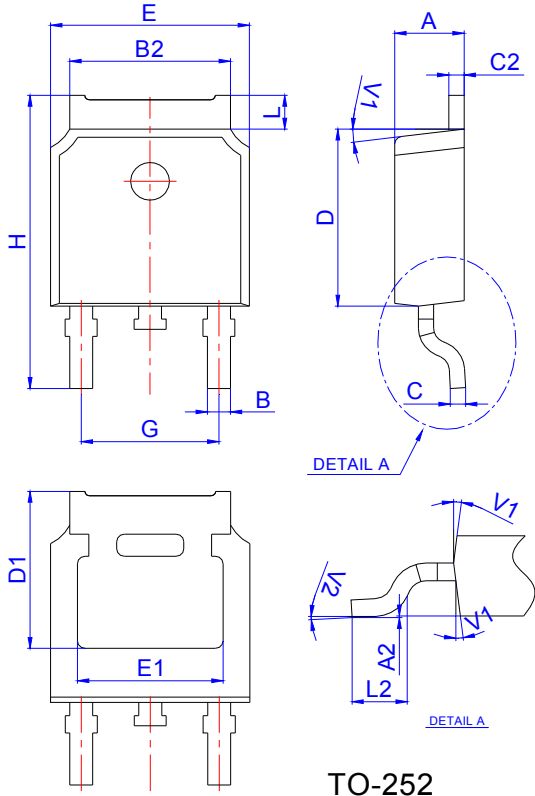
Figure 4: Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM100N15KQ-R	100N15	TO-252	Tape&Reel	2500/Reel

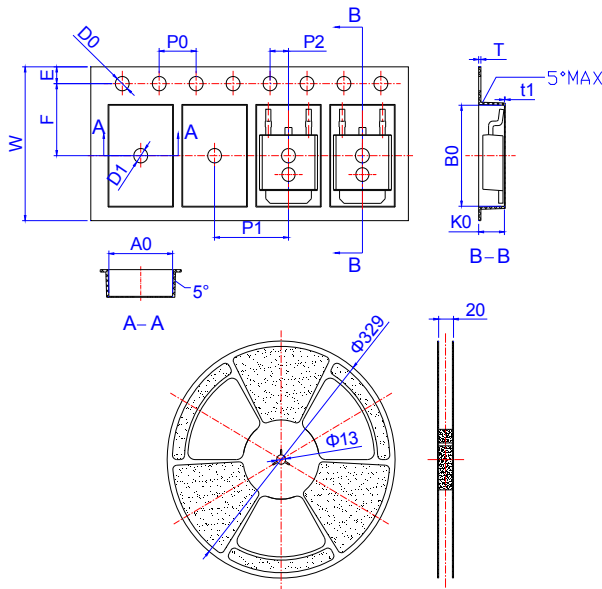
PACKAGE	MARKING
TO-252	 <p>AS □□□ → Lot Number 100N15 □□□□ → Date Code</p>

Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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